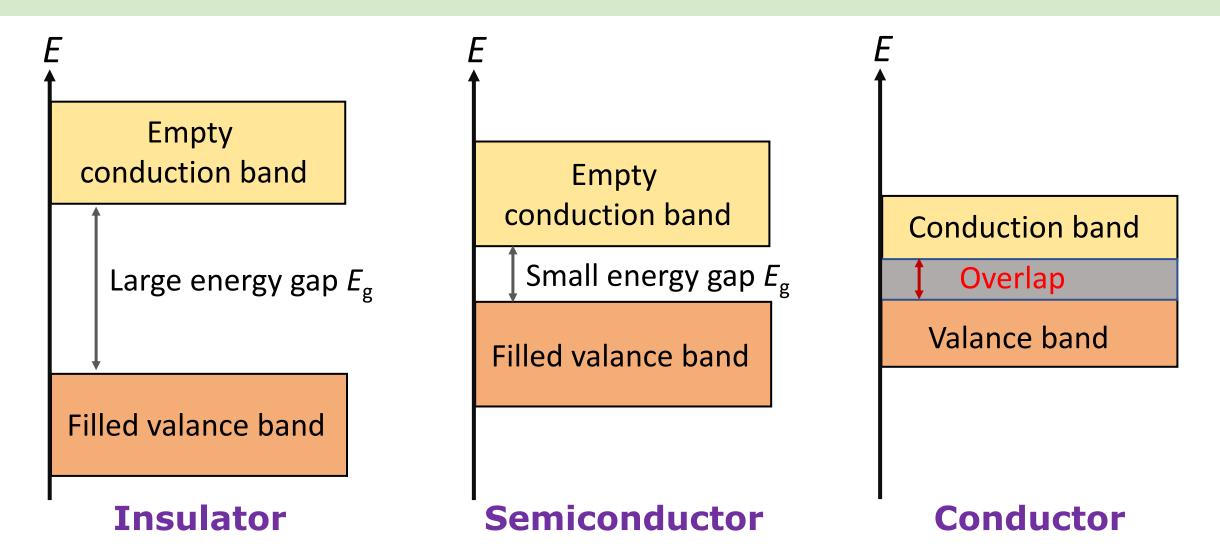
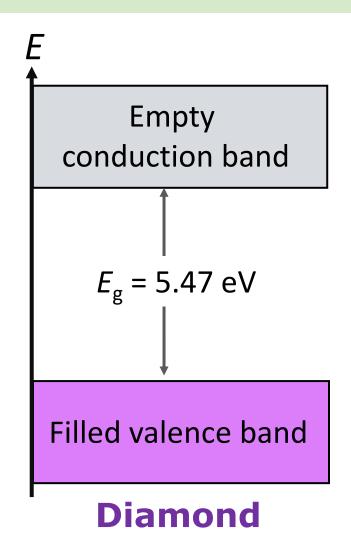
Intrinsic and extrinsic semiconductors

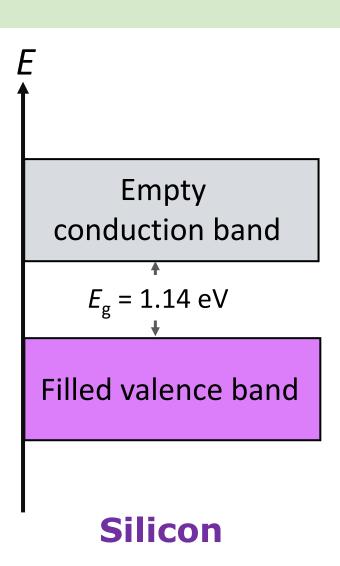
Dr Mohammad Abdur Rashid

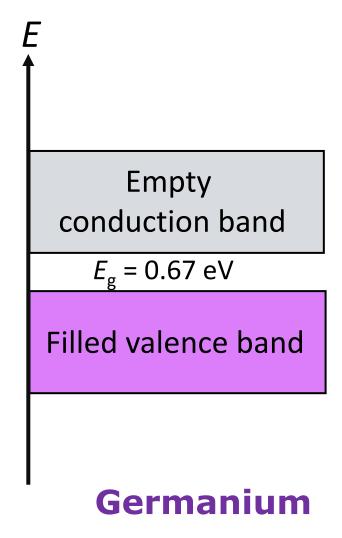
Energy Bands for Solids



Semiconductor







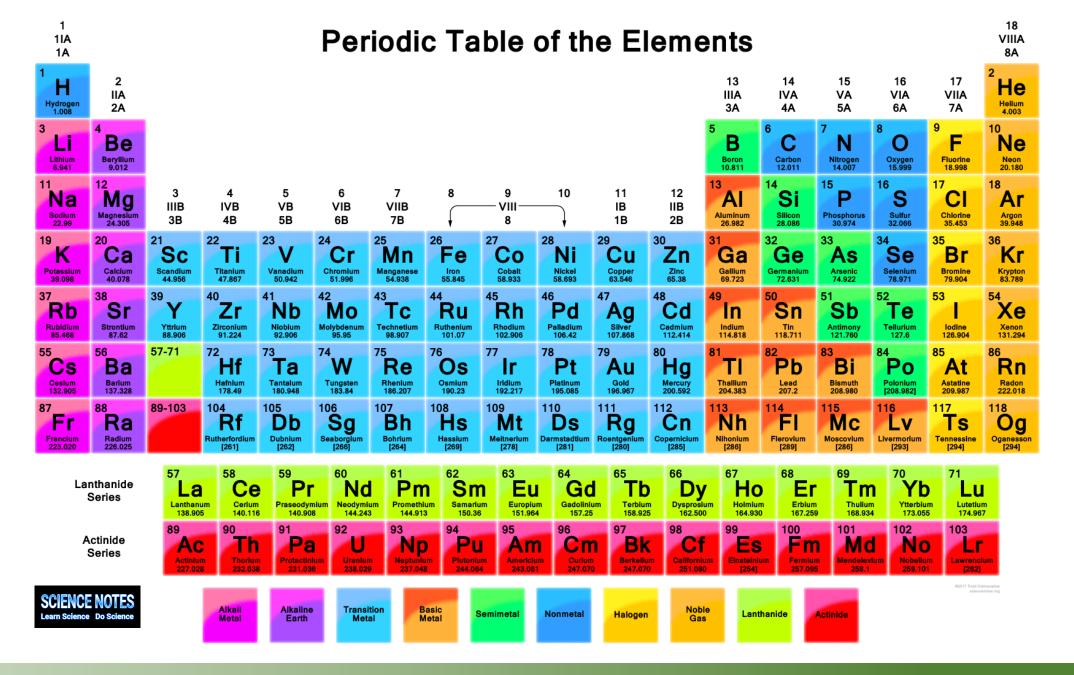
Semiconductor

Semiconductor	InSb	GaAs	GaP	ZnSe
E _g (eV)	0.18	1.42	2.25	2.7

$$E = k_B T$$

$$1 \text{ eV} = 1.6 \times 10^{-19} \text{ J}$$

 $300 \text{ K} \approx 0.026 \text{ eV}$



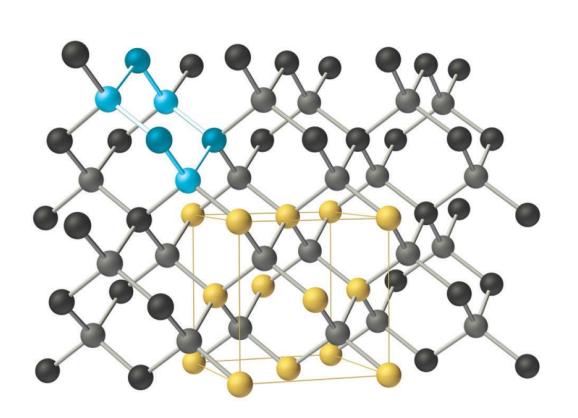


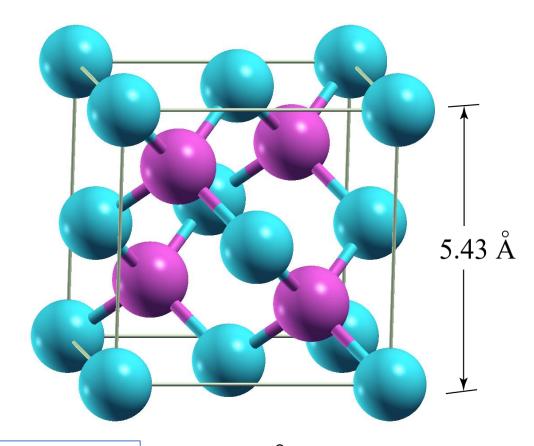
Silicon





Crystal Silicon





chem.libretexts.org

3sp tetrahedral bond

 2.35\AA

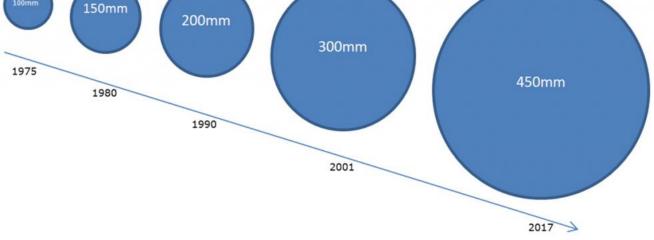


Silicon ingot

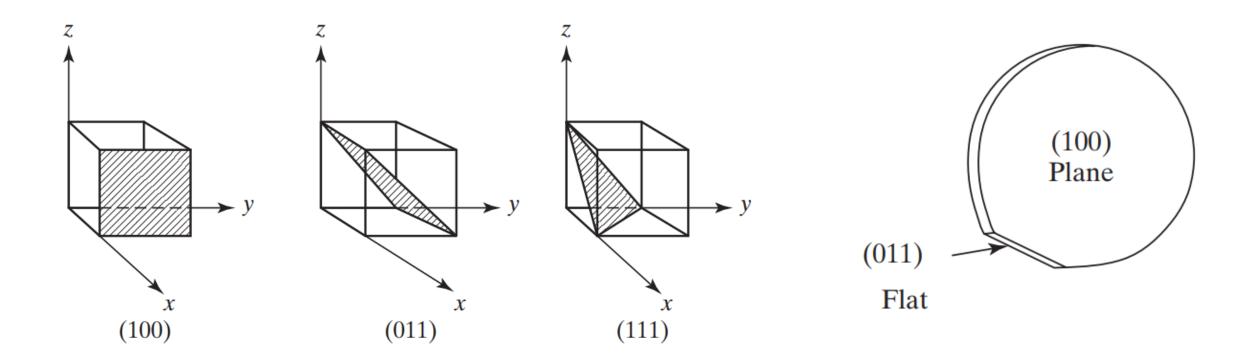


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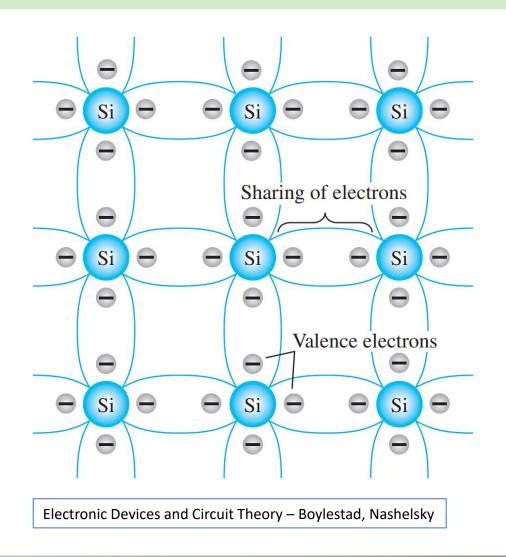


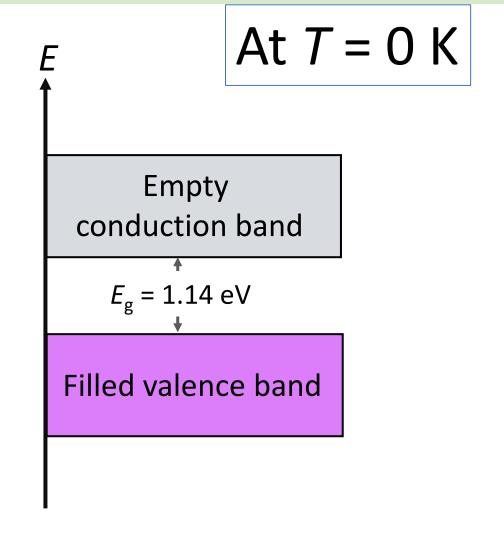
Silicon wafers



Modern Semiconductor Devices for Integrated Circuits – C. Hu

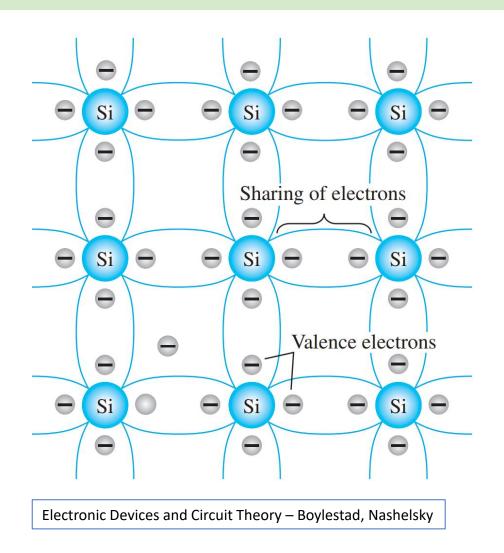
Covalent bonding of the silicon atom

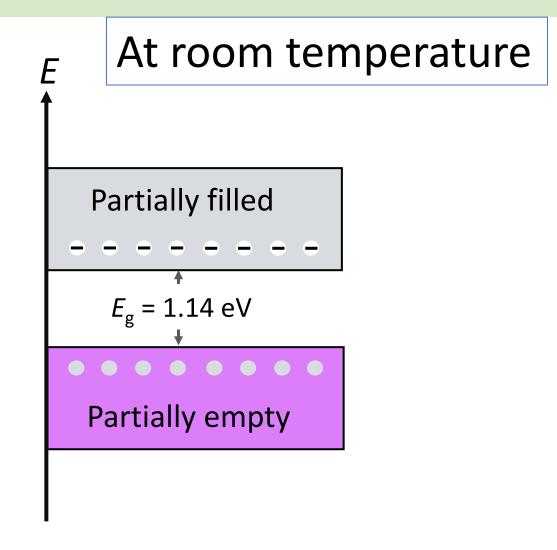




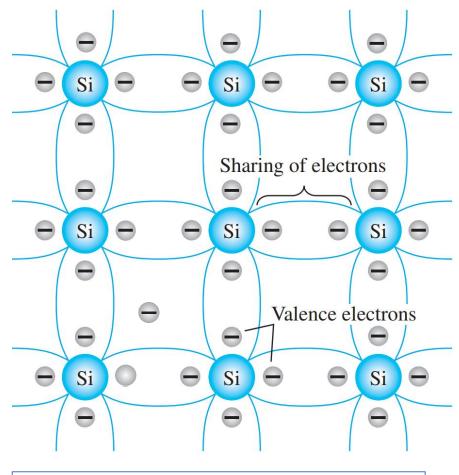
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Electron and Hole in intrinsic silicon





Electron and Hole in intrinsic silicon



Electronic Devices and Circuit Theory – Boylestad, Nashelsky

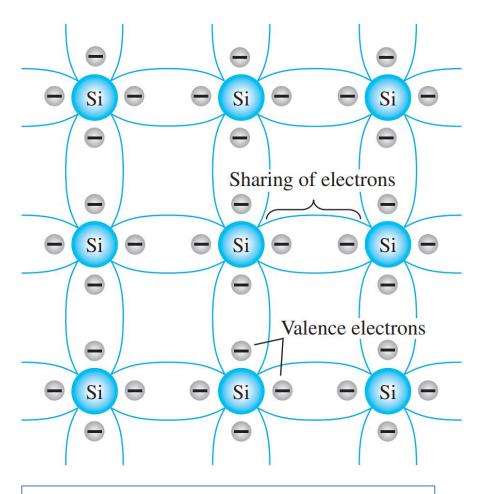
Jashore University of Science and Technology

The external causes include effects such as light energy in the form of photons and thermal energy (heat) from the surrounding medium.

At room temperature there are approximately 1.5×10^{10} free carriers in 1 cm³ of *intrinsic* silicon.

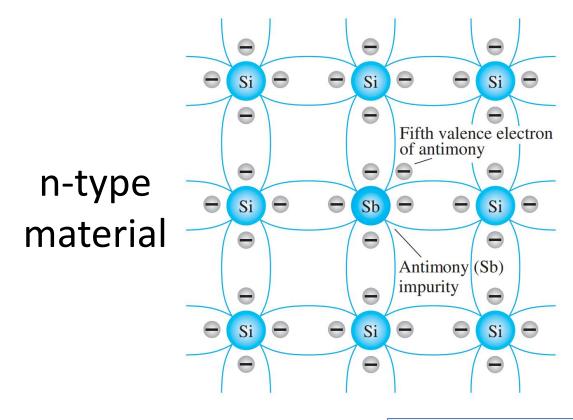
12

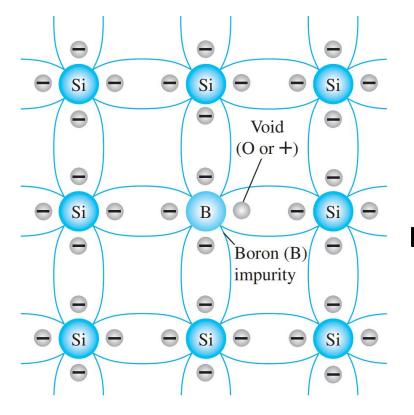
Extrinsic semiconductor



	IIIA	IVA	VA	VIA
	5	6	7	8
	В	С	Ν	0
	13	14	15	16
IIB	Al	Si	Р	S
30	31	32	33	34
Zn	Ga	Ge	As	Se
48	49	50	51	52
Cd	In	Sn	Sb	Те

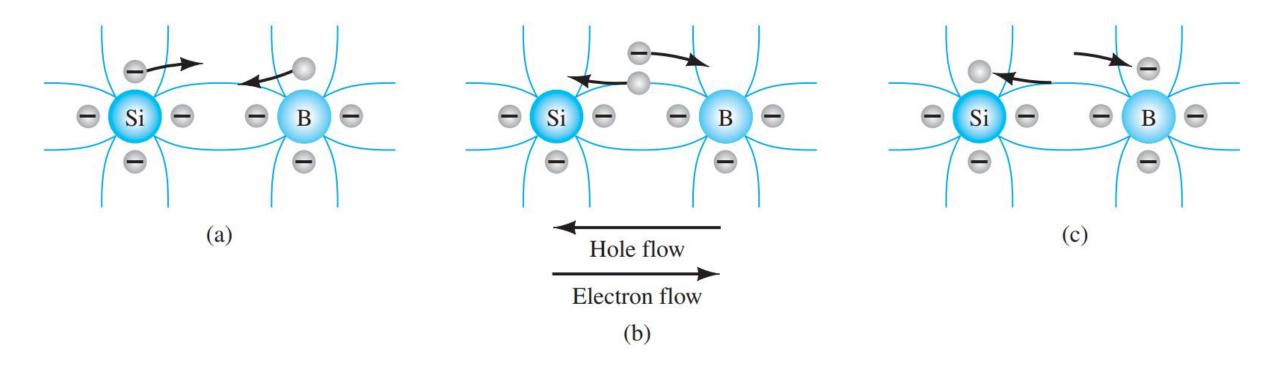
Extrinsic semiconductor





p-type material

Electron versus Hole Flow



Majority and Minority Carriers

